

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3790	438/257.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:23
L2	3681	1 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:24
L3	119	2 and (gate near electrode) and (source near electrode) and (drain near electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:25
L4	900	438/259.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:25
L5	886	4 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:25
L6	97	5 and (gate near electrode) and (source near electrode) and (drain near electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:25
L7	347	438/263.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26

L8	343	7 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26
L9	12	8 and (gate near electrode) and (source near electrode) and (drain near electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26
L10	329	438/265.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26
L11	317	10 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26
L12	6573	257/314-316.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26
L13	6184	12 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:26
L14	410	13 and (gate near electrode) and (source near electrode) and (drain near electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:27
L15	1462	257/324.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:28

L16	1400	15 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:28
L17	14481	(method) with (semiconductor near packag\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:29
L18	43704	(method) with ((field- effect near transistor (field near effect near transistor) (tft))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:30
L19	11045	18 and (gate near electrode) and (source near electrode) and (drain near electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:30
L20	10655	19 and (substrate wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:30
L21	27	1 and 20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/15 16:30
S1	31356	((silicon near oxynitride) (silicon near oxy-nitride) (sion)) and (cvd or ald or chemical near vapor near deposition or atomic near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 10:42

S2	23	((cvd) (chemical near vapor near deposition)) and ((silicon near oxynitride) (silicon near oxy-nitride) (sion)) and ((chlorosilane) (chlor\$1 near3 silane) (dichlorosilane) (hexachlorosilane) (trichlorosilane)) and (oxidiz\$3 oxygen) and (nitrid\$3 nitrogen)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 10:45
S5	3	S4 and (excitation near period) and (exciting near mechanism)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 10:50
S6	4	"6342133".pn. "4874493".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/02 19:15

6/ 15/ 2009 4:32:30 PM

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